

# SID Mid Europe Meeting

from 9–10 October 2014  
in Stuttgart, Germany

## Program

### Thursday, October 9th

10:00-10:30	<b>Registration and Coffee</b>		
10:30-10:40	<b>Welcome and Opening Remarks</b>	Norbert Fruehauf	University of Stuttgart, Germany
	<b>OLED I</b>		
10:40-11:10	Invited Novaleds materials contribution to OLED displays and latest developments towards fully flexible VOFET driven AMOLED displays	Gregor Schwartz	Novalied GmbH, Germany
11:10-11:30	High resolution OLED micro-patterning for microdisplays and micro-signage	Uwe Vogel	Fraunhofer COMEDD, Germany
	<b>Liquid Crystal Technologies</b>		
11:30-11:50	Nematic liquid crystal devices with sub-millisecond response time	Jeroen Beeckman	Ghent University, Belgium
11:50-12:10	Conformable LCD for embedding inside a contact lens	Herbert de Smet	Ghent University, Belgium
12:10-12:30	Liquid crystals for microwave applications	Michael Wittek	Merck KGaA, Germany
12:30-13:30	<b>Lunch Break</b>		
	<b>Flexible Electronics</b>		
13:30-14:00	Invited Ultra-flexible sensing systems based on low temperature polysilicon electronics: from material selection to device application	Luca Maiolo	Consiglio Nazionale delle Ricerche, Italy
14:00-14:20	Organic TFT backplanes for different display applications	Burag Yaglioglu	Plastic Logic Ltd., UK
14:20-14:40	Stability of organic thin-film transistors for CMOS circuits	Michael Strecker	University of Stuttgart, Germany
14:40-15:20	<b>Coffee Break</b>		
	<b>OLED II</b>		
15:20-15:40	The art of OLED device making	Armin Wedel	Fraunhofer IAP, Germany
15:40-16:00	Multilayer graphene based flexible passive matrix OLED displays	Suleyman Celik	Sabanci University, Turkey
16:00-16:30	<b>SID ME Chapter 20th Anniversary Ceremony</b>		
16:45-17:15	<b>Transfer to Cannstatter Wasen</b>		

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### Friday, October 10th

#### Oxide Electronics I

9:00-9:30	Invited	Amorphous oxide electronics	Arokia Nathan	University of Cambridge, UK
9:30-10:00	Invited	Post processes for high performance and stable solution-processed oxide TFTs	Hyun Jae Kim	Yonsei University, South Korea

10:00-10:40

#### Coffee Break

#### Oxide Electronics II

10:40-11:00		Effect of hydrogen diffusion from SiO <sub>x</sub> etch-stopper layer on amorphous In-Ga-Zn-O thin-film transistor properties	Tatsuya Toda	Kochi University, Japan
11:00-11:20		Integrated circuits using oxygen barrier stabilized oxide TFTs	Marcus Herrmann	University of Stuttgart, Germany
11:20-11:50	Invited	Low temperature technology for nanostructured ZnO thin-film phosphor fabrication	Chaoyang Li	Kochi University, Japan

#### Display Measurement and Optimization

11:50-12:10		Optimization of reference voltages for TFT-LCD source drivers with a 3-dimensional flicker analysis	Hans-Ulrich Lauer	Johnson Controls Automotive Electronics GmbH, Germany
12:10-12:30		Measurements of flexible displays – challenges and solutions	Karlheinz Blankenbach	Pforzheim University, Germany
12:30-12:50		Viewing properties of flexible AMOLEDs	Jyrki Kimmel	Nokia Labs, Finland
12:50-13:00		Summary		